

# SEMiX241DH16s



SEMiX® 13

## Bridge Rectifier Module (halfcontrolled) SEMiX241DH16s

### Features

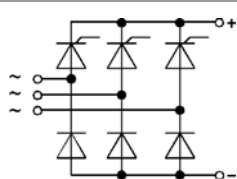
- Terminal height 17 mm
- Chips soldered directly to isolated substrate
- UL recognised file no. E63532

### Typical Applications\*

- Input Bridge Rectifier for AC/DC motor control
- Power supply

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
<b>Chip</b>				
$I_D$	$T_j = 130\text{ °C}$ sinus 180°	$T_c = 85\text{ °C}$	240	A
		$T_c = 100\text{ °C}$	200	A
$I_{TSM}$	10 ms	$T_j = 25\text{ °C}$	2250	A
		$T_j = 130\text{ °C}$	1900	A
$i^2t$	10 ms	$T_j = 25\text{ °C}$	25300	A <sup>2</sup> s
		$T_j = 130\text{ °C}$	18000	A <sup>2</sup> s
$V_{RSM}$			1700	V
$V_{RRM}$			1600	V
$V_{DRM}$			1600	V
$(di/dt)_{cr}$	$T_j = 130\text{ °C}$		100	A/μs
$(dv/dt)_{cr}$	$T_j = 130\text{ °C}$		1000	V/μs
$T_j$			-40 ... 130	°C
<b>Module</b>				
$T_{stg}$			-40 ... 125	°C
$V_{isol}$	AC sinus 50Hz	1 min	4000	V
		1 s	4800	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Chip</b>						
$V_T$	$T_j = 25\text{ °C}$ , $I_T = 300\text{ A}$				1.9	V
$V_{T(TO)}$	$T_j = 130\text{ °C}$				0.85	V
$r_T$	$T_j = 130\text{ °C}$				4	mΩ
$I_{DD}; I_{RD}$	$T_j = 130\text{ °C}$ , $V_{DD} = V_{DRM}$ ; $V_{RD} = V_{RRM}$				24	mA
$t_{gd}$	$T_j = 25\text{ °C}$ , $I_G = 1\text{ A}$ , $di_G/dt = 1\text{ A}/\mu\text{s}$			1		μs
$t_{gr}$	$V_D = 0.67 \cdot V_{DRM}$			2		μs
$t_q$	$T_j = 130\text{ °C}$			150		μs
$I_H$	$T_j = 25\text{ °C}$			150	250	mA
$I_L$	$T_j = 25\text{ °C}$ , $R_G = 33\text{ }\Omega$			300	600	mA
$V_{GT}$	$T_j = 25\text{ °C}$ , d.c.		3			V
$I_{GT}$	$T_j = 25\text{ °C}$ , d.c.		150			mA
$V_{GD}$	$T_j = 130\text{ °C}$ , d.c.				0.25	V
$I_{GD}$	$T_j = 130\text{ °C}$ , d.c.				6	mA
$R_{th(j-c)}$	sin. 180°	per thyristor			0.32	K/W
		per diode			0.32	K/W
<b>Module</b>						
$R_{th(c-s)}$	per chip					K/W
	per module			0.04		K/W
$M_s$	to heat sink (M5)		3		5	Nm
$M_t$	to terminals (M6)		2.5		5	Nm
$a$					5 * 9,81	m/s <sup>2</sup>
$w$				350		g



DH

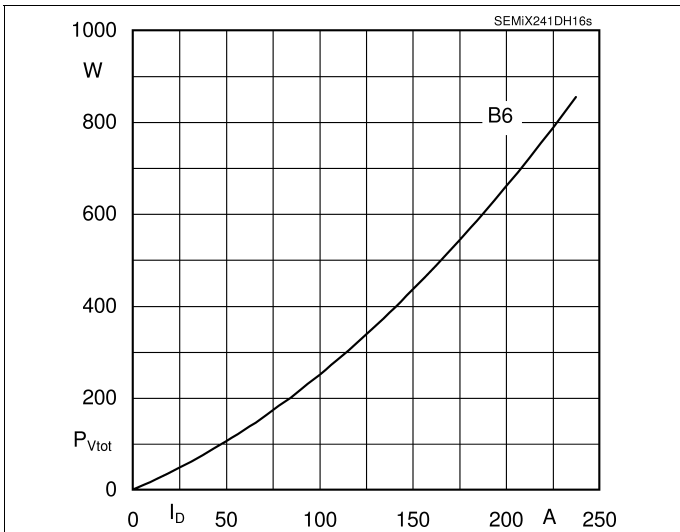


Fig. 4L: Power dissipation per module vs. direct current

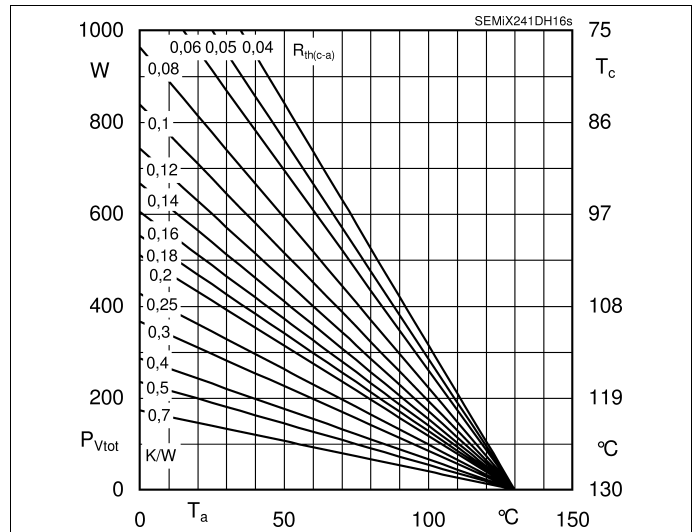


Fig. 4R: Power dissipation per module vs. case temperature

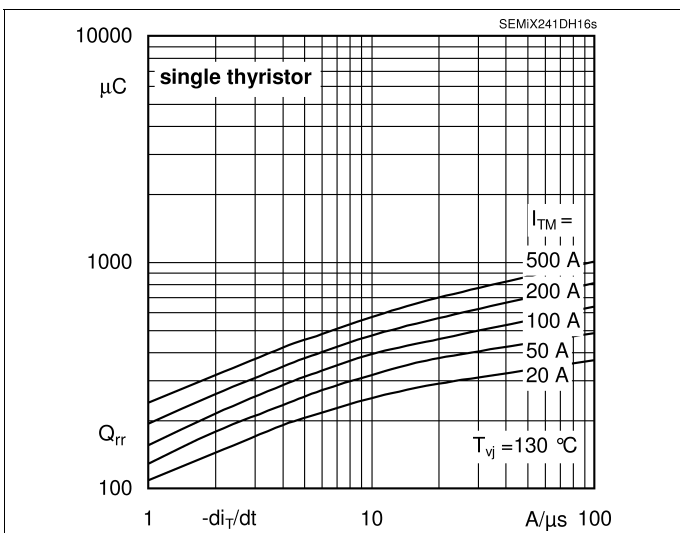


Fig. 5: Recovered charge vs. current decrease

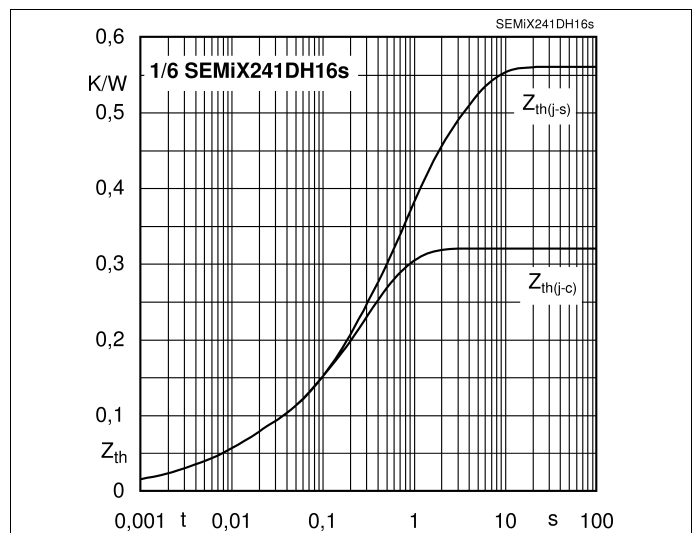


Fig. 6: Transient thermal impedance vs. time

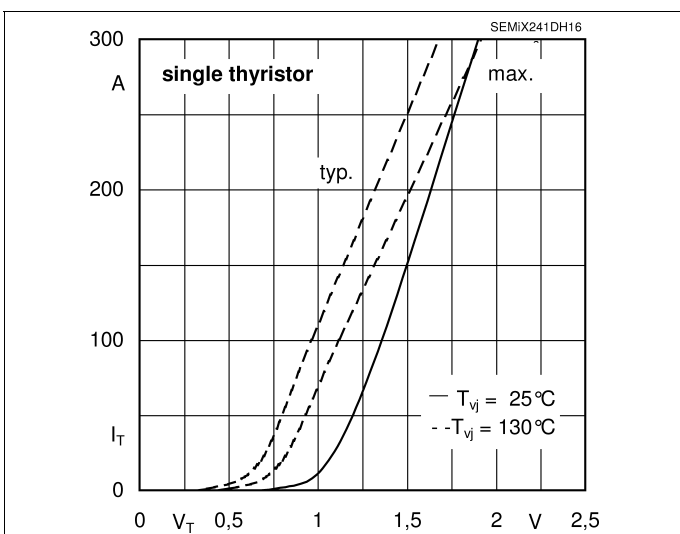


Fig. 7: On-state characteristics

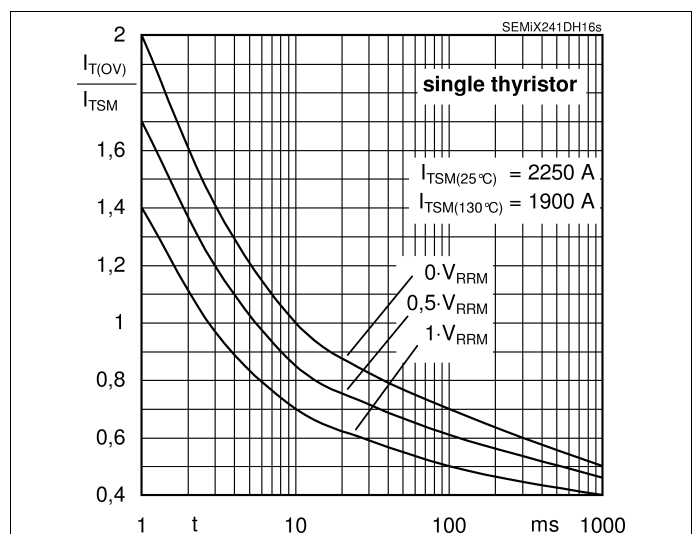


Fig. 8: Surge overload current vs. time

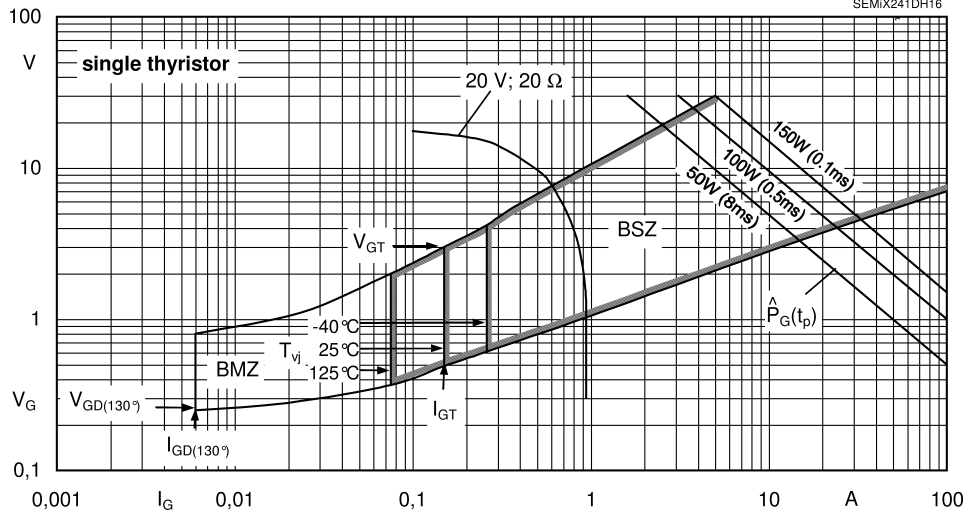
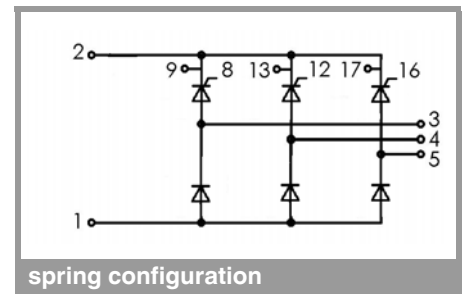
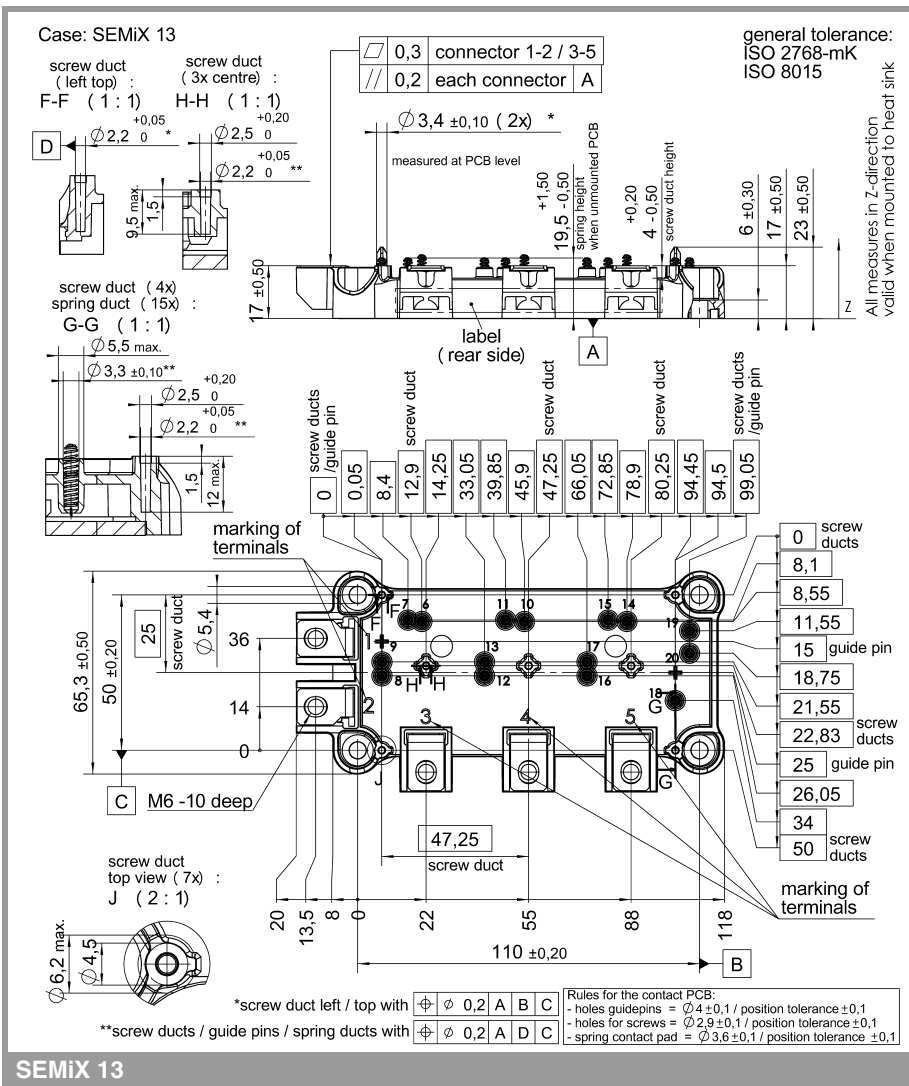


Fig. 9: Gate trigger characteristics



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

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